

ABSTRACT

Assist Features for use in Lithographic Projection

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In a mask pattern for a device such as a DRAM including a nearly regular array of isolated features, assist features are positioned so as to make the array more symmetric. Where the isolated features are positioned at most but not all of the points of a regular unit cell, the assist features may be positioned at the points of the unit cell not occupied by the isolated features. The isolated features may represent contact holes.

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